

Turn-on losses and times:

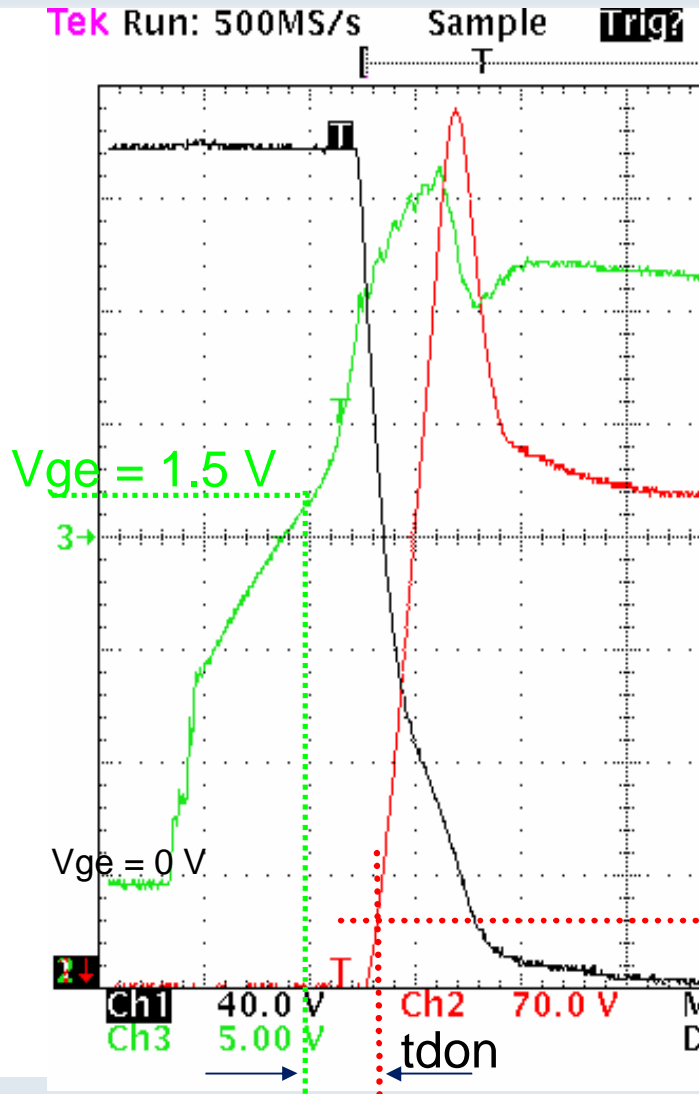
- Values unchanged as compared to datasheet

Turn-off losses:

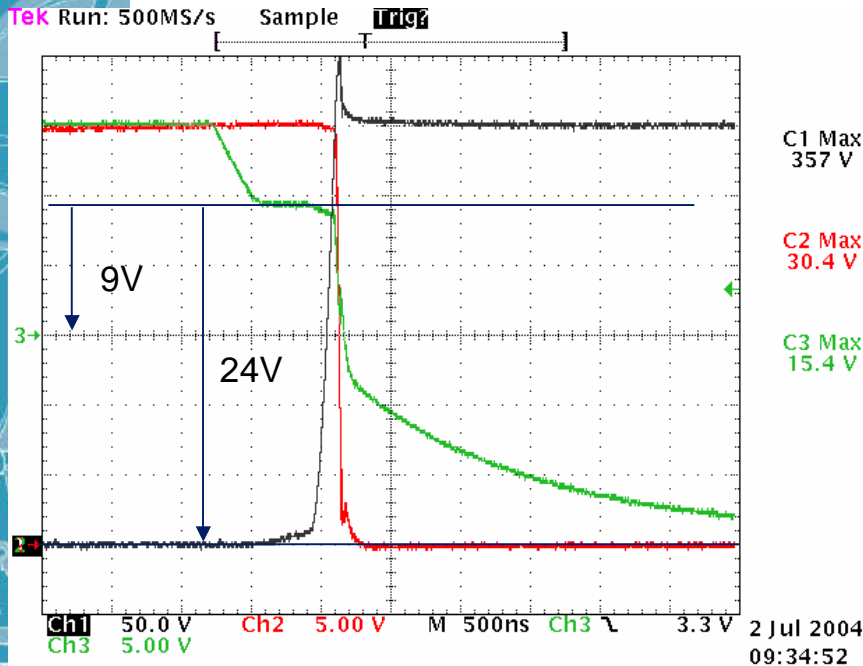
- Switching to 0V corresponds roughly to switching to -15V with $3 \times R_g$
 - with nominal R_g roughly $E_{\text{off}} + 10\%$ vs. datasheet

Gate charge:

- reduced by 40% vs. datasheet ($V_{\text{CC}} = 300\text{V}$)



- turn-on delay time is defined from $V_{ge} = 1.5\text{ V}$ to $I_c = 10\%$
-> no difference between 0/15 V and +/- 15 V switching!
- Energy is determined by switching trajectory for $V_{ge} > V_{ge_{th}}$.
- Then $I_{gate} = 15\text{ V} - V_{ge}$
-> no difference between 0/15 V and +/- 15 V switching!

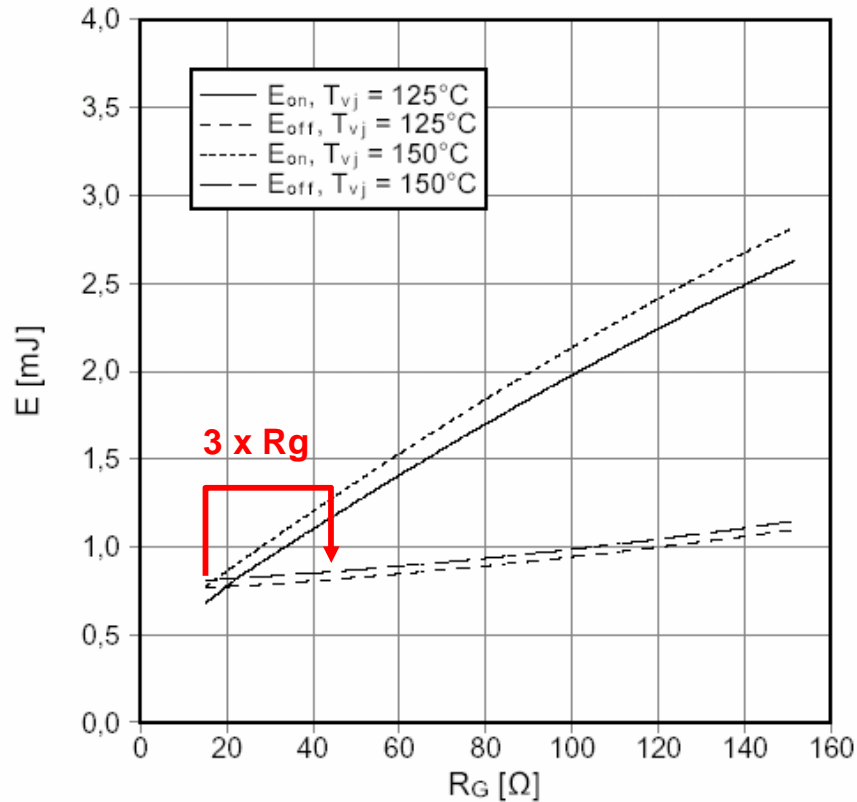


- for 0V switching turn-off delay time is increased by a factor of 2-3 vs. datasheet. Reason: decreased gate current due to decreased voltage on gate resistor (8-15 V instead of 23-30 V!)
- Energy corresponds to E_{off} at $R_g = \text{approx. } 3 \times R_g$ given in the datasheet: Reason: Voltage ratio (9 V / 24 V leads to the same decrease in gate current as a 3-times higher R_g value!

Schaltverluste IGBT-Wechselr. (typisch)
 switching losses IGBT-Inverter (typical)

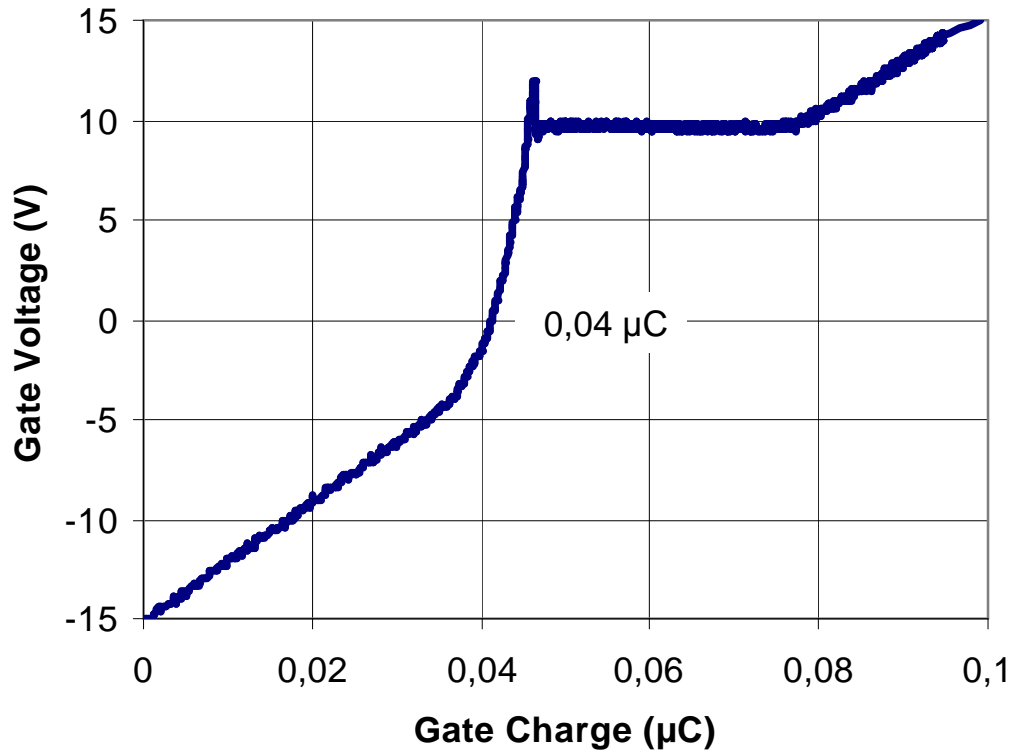
$E_{on} = f(R_G)$, $E_{off} = f(R_G)$

$V_{GE} = \pm 15 \text{ V}$, $I_C = 30 \text{ A}$, $V_{CE} = 300 \text{ V}$



- Typically, E_{off} is increased by less than 10 % with switching to 0V instead of -15V
- Note: E_{on} is unchanged!

Gate Charge curve - IGBT3 / 600V ($V_{cc} = 300V$)



- Gate charge is reduced by 40 % as compared to datasheet value (+/-15 V switching) (IGBT3 / 600V)